

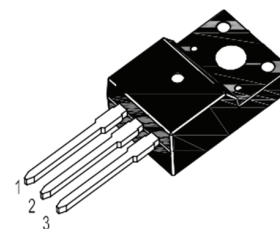
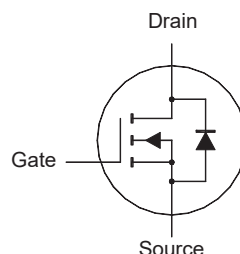
N-Channel Enhancement Mode MOSFET

Features

- High Speed Power Switching
- Halogen and Antimony Free(HAF), RoHS compliant

Application

- Hard Switching and High Speed Circuit
- DC/DC in Telecoms and Industrial



1.Gate 2.Drain 3.Source
TO-220F Plastic Package

Key Parameters

Parameter	Value	Unit
BV_{DSS}	120	V
$R_{DS(ON)}$ Max	6.2 @ $V_{GS} = 10$ V	m Ω
$V_{GS(th)}$ typ	1.7	V
Q_g typ	71.4 @ $V_{GS} = 10$ V	nC

Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	120	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	47 30	A
Peak Drain Current, Pulsed ¹⁾	I_{DM}	360	A
Avalanche Current	I_{AS}	33.6	A
Single-Pulsed Avalanche Energy ²⁾	E_{AS}	282	mJ
Power Dissipation	P_D	22.3	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	5.6	$^\circ\text{C/W}$
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	43	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width ≤ 100 μs , Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.

²⁾ Limited by $T_{J(MAX)}$, starting $T_J = 25^\circ\text{C}$, $L = 0.5$ mH, $R_g = 25$ Ω , $I_{AS} = 33.6$ A, $V_{GS} = 10$ V.

³⁾ Device Surface Mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate, in a still air.

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $I_D = 250\ \mu\text{A}$	BV_{DSS}	120	-	-	V
Drain-Source Leakage Current at $V_{DS} = 120\ \text{V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current at $V_{GS} = \pm 20\ \text{V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	$V_{GS(th)}$	1.2	-	2.5	V
Drain-Source On-State Resistance at $V_{GS} = 10\ \text{V}$, $I_D = 20\ \text{A}$	$R_{DS(on)}$	-	5	6.2	m Ω
DYNAMIC PARAMETERS					
Forward Transconductance at $V_{DS} = 5\ \text{V}$, $I_D = 20\ \text{A}$	g_{fs}	-	53	-	S
Gate resistance at $V_{GS} = 0\ \text{V}$, $V_{DS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	R_g	-	1	-	Ω
Input Capacitance at $V_{GS} = 0\ \text{V}$, $V_{DS} = 60\ \text{V}$, $f = 1\ \text{MHz}$	C_{iss}	-	3606	-	pF
Output Capacitance at $V_{GS} = 0\ \text{V}$, $V_{DS} = 60\ \text{V}$, $f = 1\ \text{MHz}$	C_{oss}	-	598	-	pF
Reverse Transfer Capacitance at $V_{GS} = 0\ \text{V}$, $V_{DS} = 60\ \text{V}$, $f = 1\ \text{MHz}$	C_{rss}	-	34	-	pF
Gate charge total at $V_{GS} = 10\ \text{V}$, $V_{DS} = 60\ \text{V}$, $I_D = 20\ \text{A}$	Q_g	-	71.4	-	nC
Gate to Source Charge at $V_{GS} = 10\ \text{V}$, $V_{DS} = 60\ \text{V}$, $I_D = 20\ \text{A}$	Q_{gs}	-	11.7	-	nC
Gate to Drain Charge at $V_{GS} = 10\ \text{V}$, $V_{DS} = 60\ \text{V}$, $I_D = 20\ \text{A}$	Q_{gd}	-	19	-	nC
Turn-On Delay Time at $V_{GS} = 10\ \text{V}$, $V_{DS} = 60\ \text{V}$, $I_D = 20\ \text{A}$, $R_g = 10\ \Omega$	$t_{d(on)}$	-	52	-	ns
Turn-On Rise Time at $V_{GS} = 10\ \text{V}$, $V_{DS} = 60\ \text{V}$, $I_D = 20\ \text{A}$, $R_g = 10\ \Omega$	t_r	-	63	-	ns
Turn-Off Delay Time at $V_{GS} = 10\ \text{V}$, $V_{DS} = 60\ \text{V}$, $I_D = 20\ \text{A}$, $R_g = 10\ \Omega$	$t_{d(off)}$	-	42	-	ns
Turn-Off Fall Time at $V_{GS} = 10\ \text{V}$, $V_{DS} = 60\ \text{V}$, $I_D = 20\ \text{A}$, $R_g = 10\ \Omega$	t_f	-	27	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $I_S = 20\ \text{A}$, $V_{GS} = 0\ \text{V}$	V_{SD}	-	-	1.2	V
Body-Diode Continuous Current	I_S	-	-	47	A
Body-Diode Continuous Current, Pulsed	I_{SM}	-	-	360	A
Body Diode Reverse Recovery Time at $I_S = 20\ \text{A}$, $di/dt = 100\ \text{A} / \mu\text{s}$	t_{rr}	-	67	-	ns
Body Diode Reverse Recovery Charge at $I_S = 20\ \text{A}$, $di/dt = 100\ \text{A} / \mu\text{s}$	Q_{rr}	-	130	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

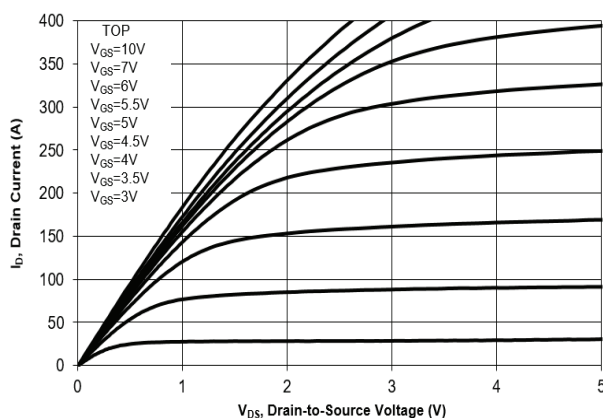


Fig. 2 Typical Transfer Characteristics

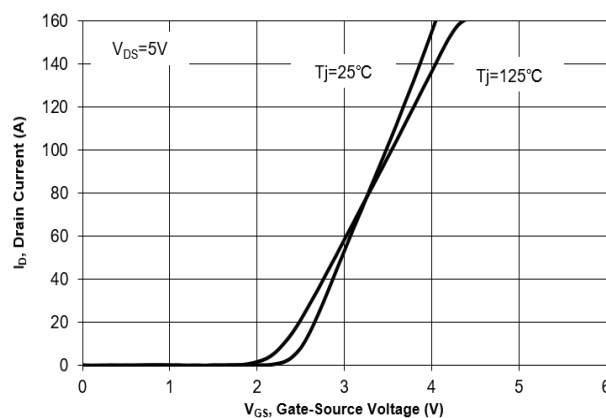


Fig. 3 on-Resistance vs Drain Current

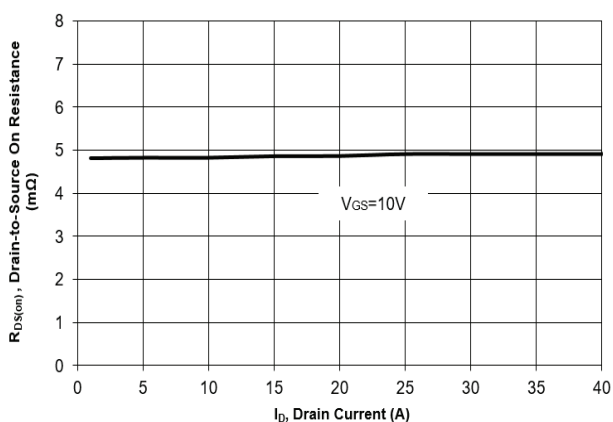


Fig. 4 on-Resistance vs. Gate to Source Voltage

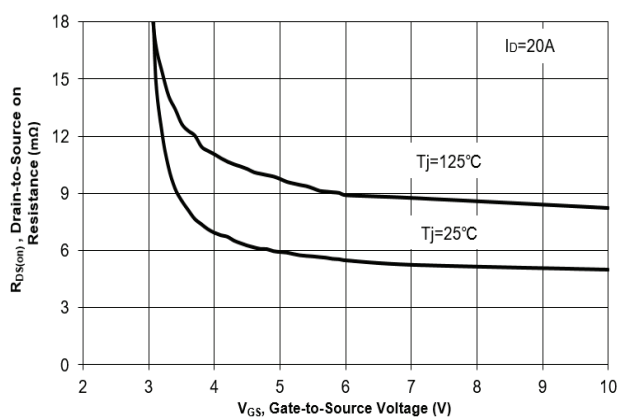


Fig. 5 on-Resistance vs. T_j

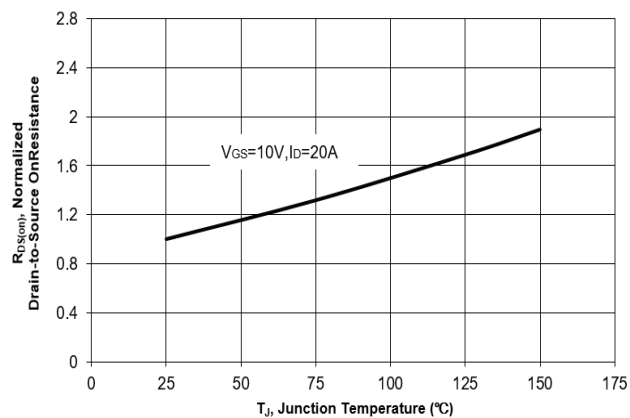
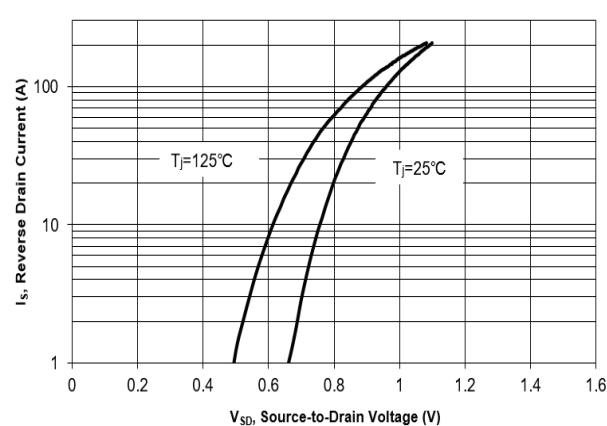


Fig. 6 Typical Body Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 13 Normalized Maximum Transient Thermal Impedance($z_{\theta JC}$)

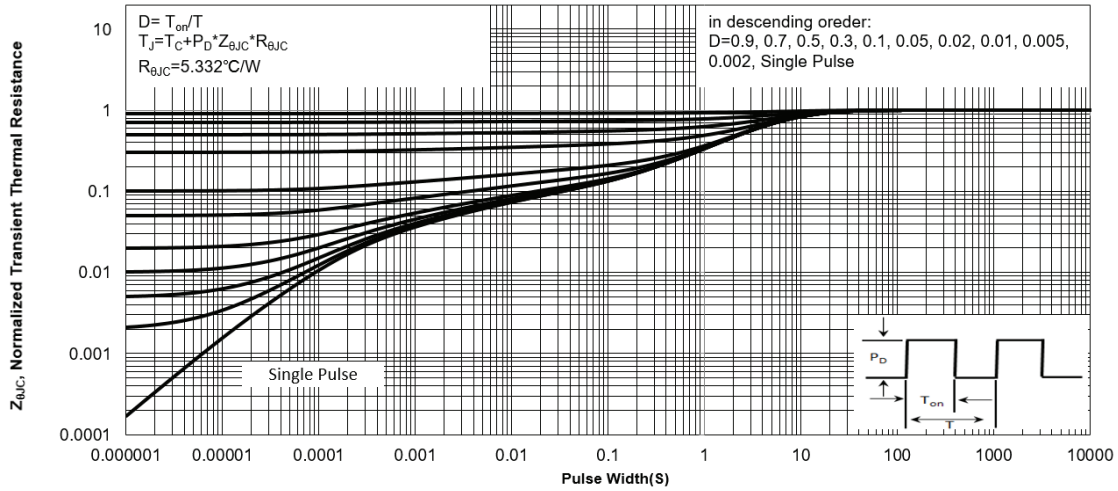
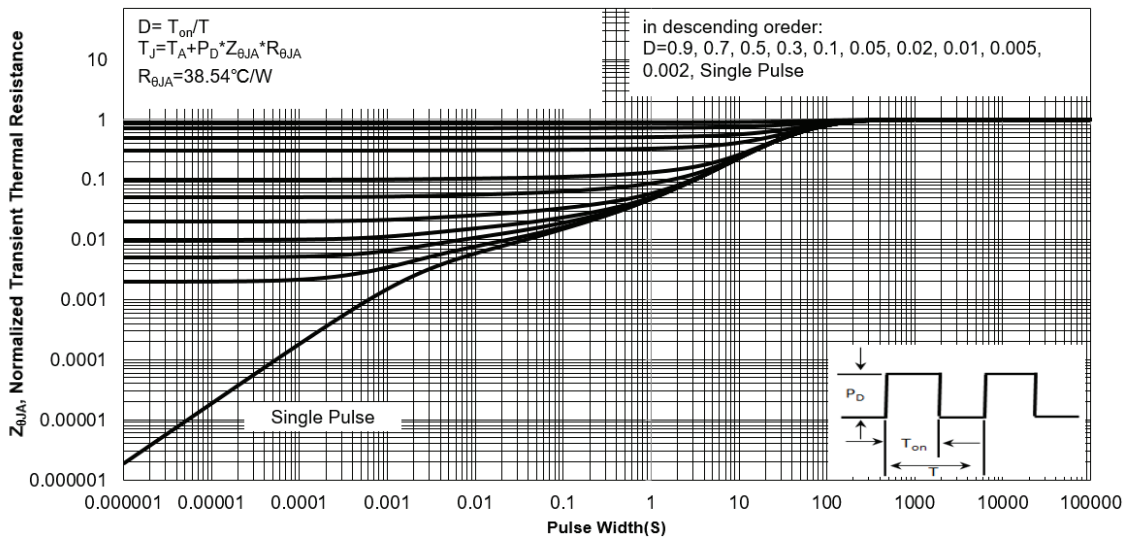
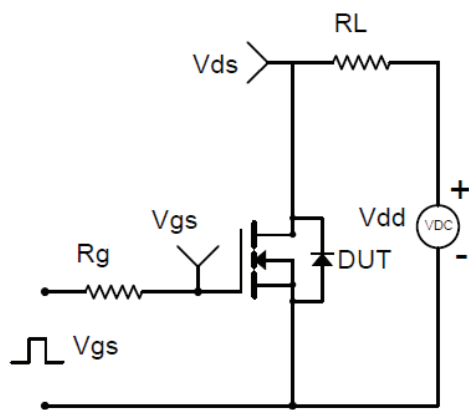
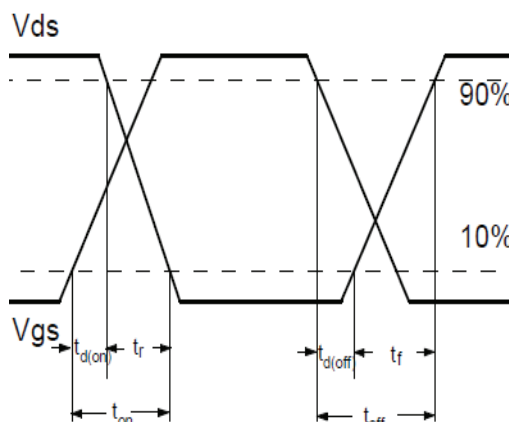
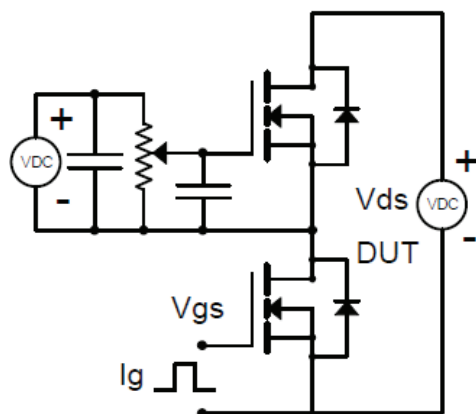
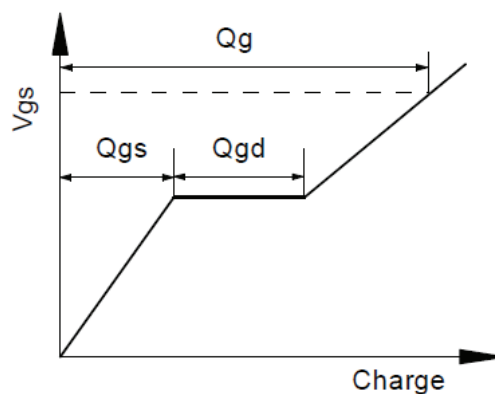
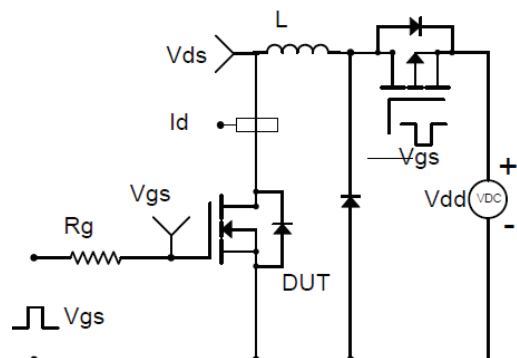
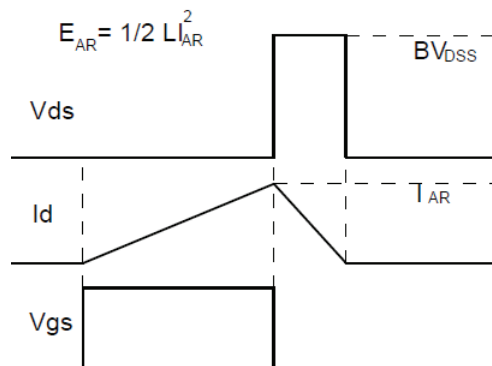


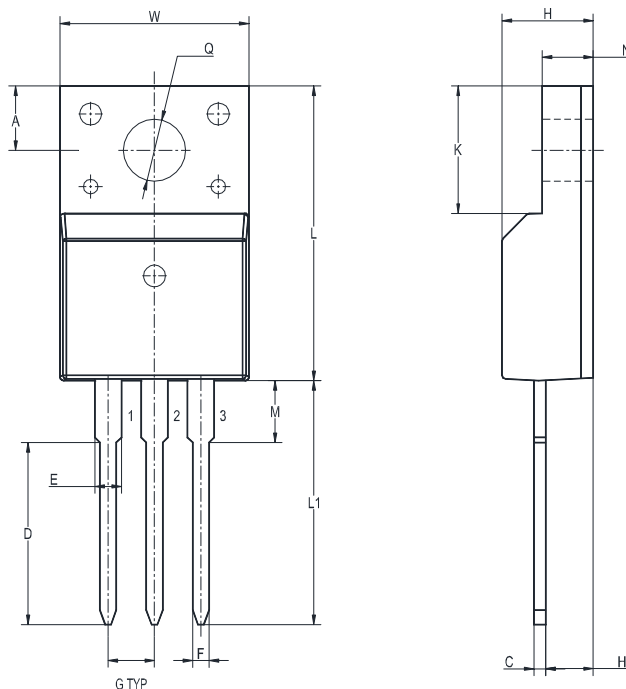
Fig. 14 Normalized Maximum Transient Thermal Impedance($z_{\theta JA}$)



Test Circuits
Fig.1-1 Switching times test circuit

Fig.1-2 Switching Waveform

Fig.2-1 Gate charge test circuit

Fig.2-2 Gate charge waveform

Fig.3-1 Avalanche test circuit

Fig.3-2 Avalanche waveform


Package Outline Dimensions (Units: mm)

TO-220F



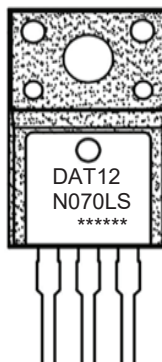
UNIT	A	C	D	E	F	G	W	H	H1	Q	L	L1	M	K	N
mm	3.5	0.7	10.3	1.5	0.9	2.54	10.5	4.9	2.9	3.4	16	13.5	3.5	6.7	2.8
	2.8	0.4	9.7	1.1	0.7	TYP.	9.5	4.5	2.5	2.9	15	12.5	2.9	6.2	2.3

Packing information

Package	Carton Quantity	Box Quantity	Base Quantity	Delivery Mode
TO-220F	5 K / Carton	1 K / Box	50 pcs / Tube	Tube

Marking information

" DAT12N070LS " = Part No.
 " ***** " = Date Code Marking
 Font type: Arial



Disclaimer: Our company reserve the right to make modifications, enhancements, improvements, corrections or other changes to improve product design, functions and reliability, anytime without notice.

Fig. 7 Typical Junction Capacitance

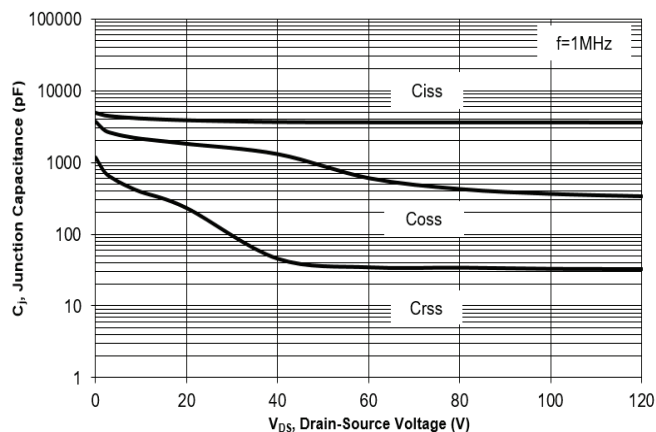


Fig. 8 Drain-Source Leakage Current vs. T_J

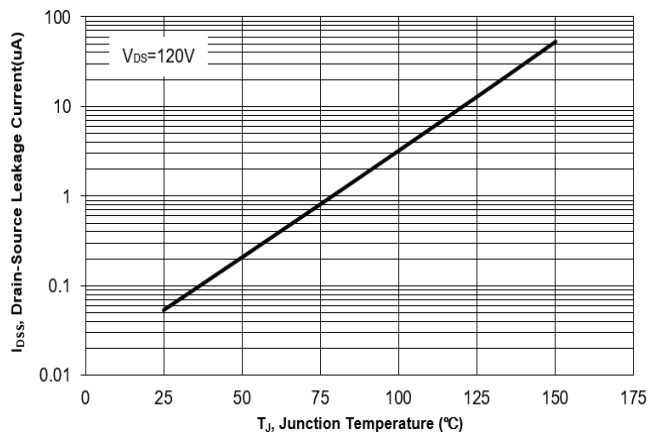


Fig. 9 $V_{(BR)DSS}$ vs. Junction Temperature

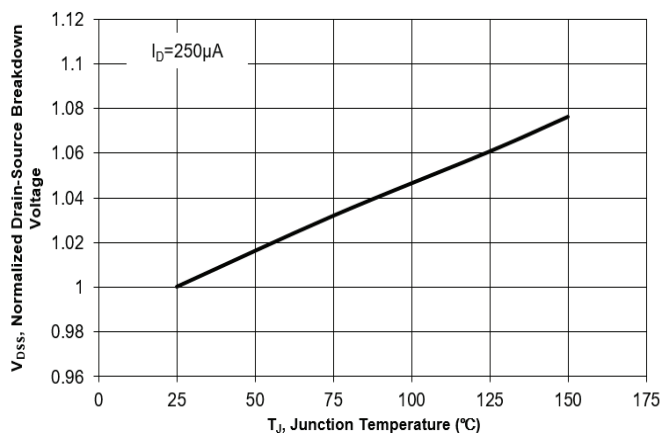


Fig. 10 Gate Threshold Variation vs. T_J

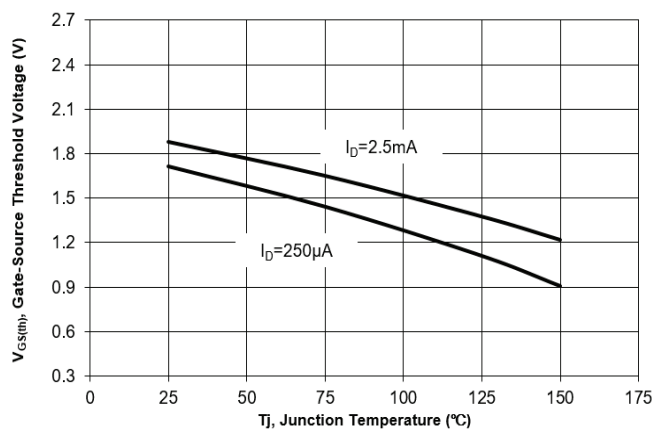


Fig. 11 Gate Charge

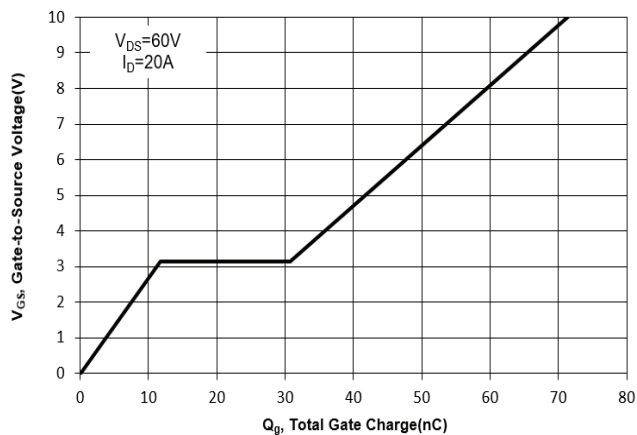


Fig. 12 Safe Operation Area

